Absolute Maximum Ratings (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	200	mA

Thermal Characteristics – Total Device (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 7) Total Device	P_D	200	mW
Thermal Resistance, Junction to Ambient (Note 7)	$R_{\theta JA}$	625	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150	°C

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

Notes: 7. For a device mounted on minimum recommended pad layout with 1oz copper that is on a single-sided 1.6mm FR4 PCB; the device is measured under still air conditions whilst operating in a steady-state.
8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics – Total Device

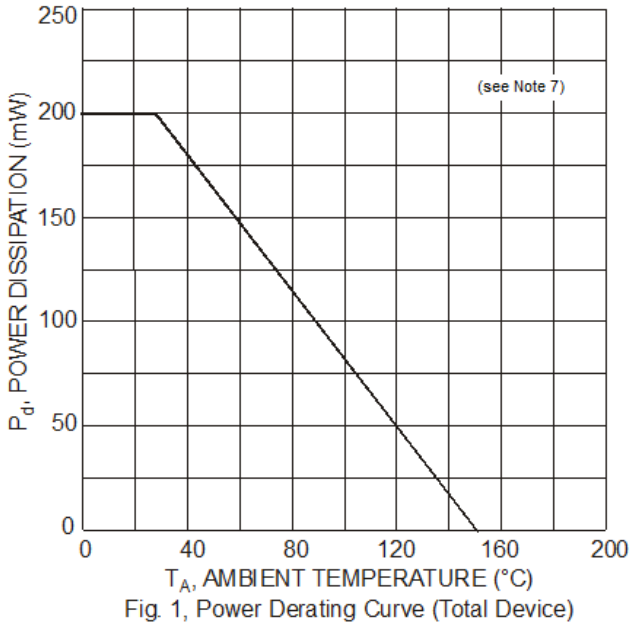

Fig. 1, Power Derating Curve (Total Device)

Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV_{CBO}	60	—	—	V	I_C = 100µA, I_E = 0
Collector-Emitter Breakdown Voltage(Note 9)	BV_{CEO}	40	—	—	V	I_C = 1.0mA, I_B = 0
Emitter-Base Breakdown Voltage	BV_{EBO}	6.0	—	—	V	I_E = 100µA, I_C = 0
Collector Cutoff Current	I_{CEX}	—	—	50	nA	V_{CE} = 30V, $V_{EB(OFF)}$ = 3.0V
Base Cutoff Current	I_{BL}	—	—	50	nA	V_{CE} = 30V, $V_{EB(OFF)}$ = 3.0V
ON CHARACTERISTICS (Note 9)						
DC Current Gain	h_{FE}	40 70 100 60 30	—	— — 300 — —	—	I_C = 100µA, V_{CE} = 1.0V I_C = 1.0mA, V_{CE} = 1.0V I_C = 10mA, V_{CE} = 1.0V I_C = 50mA, V_{CE} = 1.0V I_C = 100mA, V_{CE} = 1.0V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	—	200 300	mV	I_C = 10mA, I_B = 1.0mA I_C = 50mA, I_B = 5.0mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	0.65 —	—	850 950	mV	I_C = 10mA, I_B = 1.0mA I_C = 50mA, I_B = 5.0mA
MATCHING CHARACTERISTICS						
DC Current Gain Matching (Note 10)	h_{FE1} / h_{FE2}	—	1	2	%	I_C = 2mA, V_{CE} = 5V
Base-Emitter Voltage Matching (Note 11)	V_{BE1} - V_{BE2}	—	1	2	mV	I_C = 2mA, V_{CE} = 5V
Collector-Emitter Saturation Voltage (Note 10)	$V_{CE(SAT)1}$ / $V_{CE(SAT)2}$	—	1	2	%	I_C = 10mA, I_B = 1.0mA
Base-Emitter Saturation Voltage (Note 10)	$V_{BE(SAT)1}$ / $V_{BE(SAT)2}$	—	1	2	%	I_C = 10mA, I_B = 1.0mA
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C_{OBO}	—	—	4.0	pF	V_{CB} = 5.0V, f = 1.0MHz, I_E = 0
Input Capacitance	C_{IBO}	—	—	8.0	pF	V_{EB} = 0.5V, f = 1.0MHz, I_C = 0
Input Impedance	h_{IE}	1.0	—	10	kΩ	V_{CE} = 10V, I_C = 1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h_{RE}	0.5	—	8	x 10^{-4}	
Small Signal Current Gain	h_{FE}	100	—	400	—	
Output Admittance	h_{OE}	1.0	—	40	µS	
Current Gain-Bandwidth Product	f_T	300	—	—	MHz	V_{CE} = 20V, I_C = 10mA, f = 100MHz
Noise Figure	NF	—	—	5.0	dB	V_{CE} = 5.0V, I_C = 100µA, R_S = 1.0kΩ, f = 1.0kHz
SWITCHING CHARACTERISTICS						
Delay Time	t_D	—	—	35	ns	V_{CC} = 3.0V, I_C = 10mA, $V_{BE(OFF)}$ = -0.5V, I_{B1} = 1.0mA
Rise Time	t_R	—	—	35	ns	
Storage Time	t_S	—	—	200	ns	V_{CC} = 3.0V, I_C = 10mA, I_{B1} = I_{B2} = 1.0mA
Fall Time	t_F	—	—	50	ns	

Notes: 9. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.
10. Is the ratio of one transistor compared to the other transistor.
11. V_{BE1} - V_{BE2} is the absolute difference of one transistor compared to the other transistor.

Typical Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

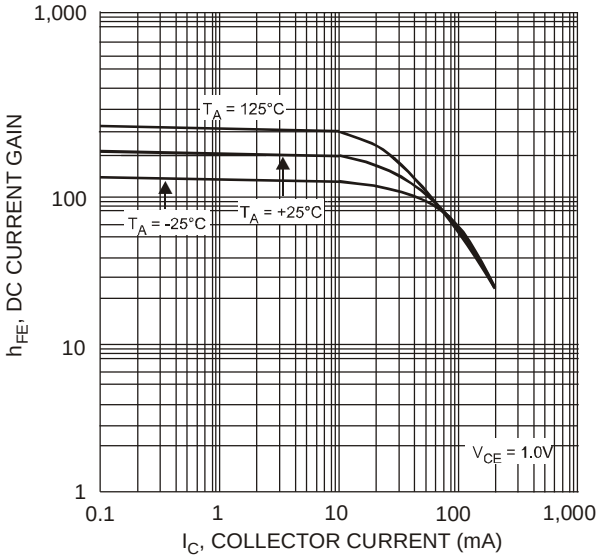

Fig. 3, Typical DC Current Gain vs. Collector Current

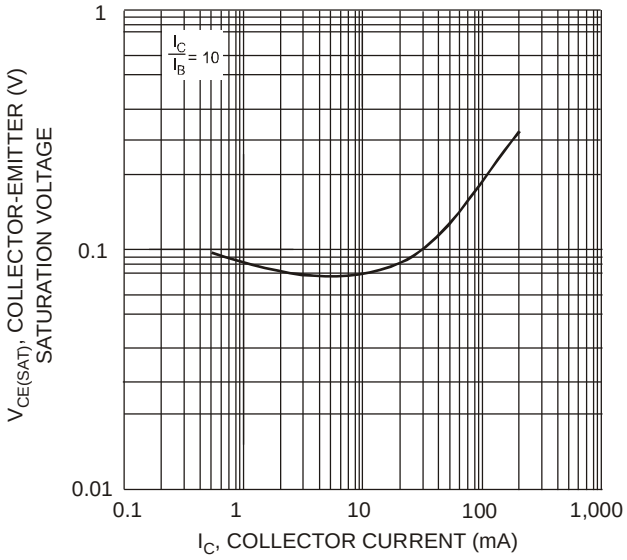

Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

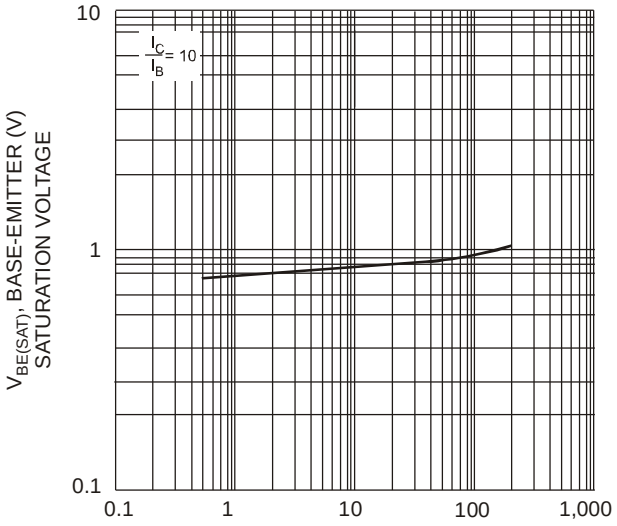

Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current

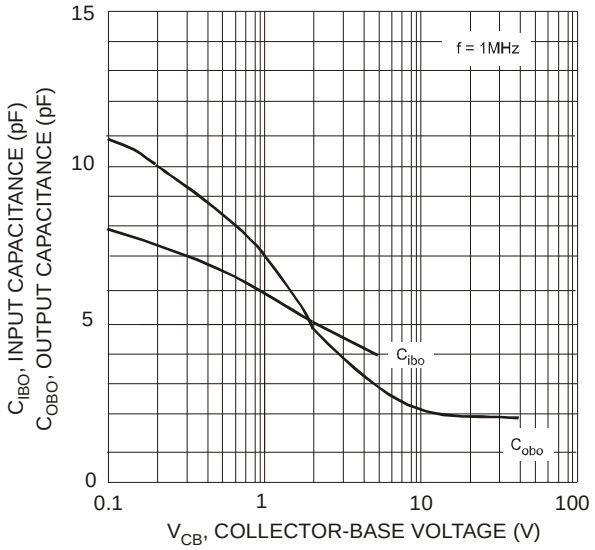

Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage

Package Outline Dimensions

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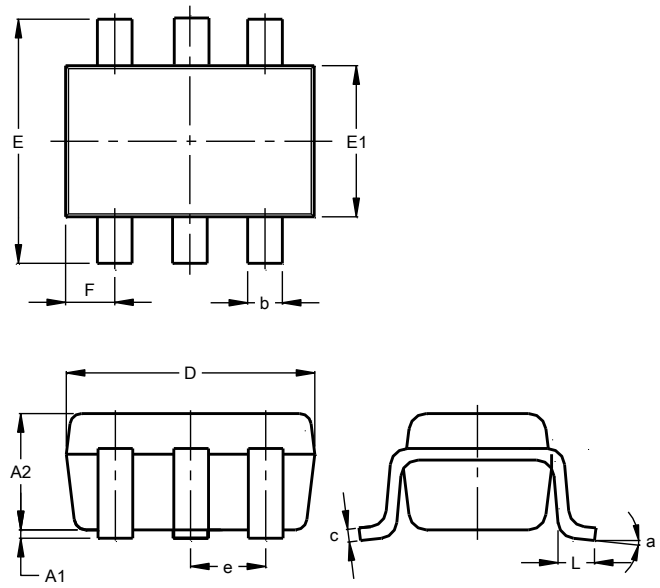

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Dim	**Min**	**Max**	**Typ**
A1	0.00	0.10	0.05
A2	0.90	1.00	1.00
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

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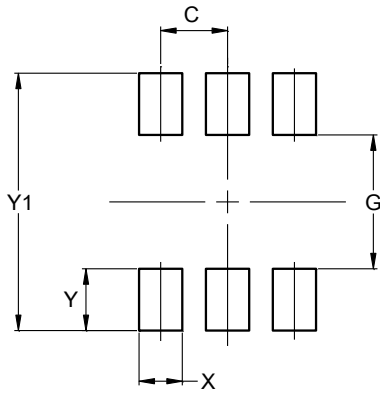

Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

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